

Silicon NPN Power Transistors

BDW83/83A/83B/83C/83D

DESCRIPTION

- With TO-3PN package
- Complement to type BDW84/84A/84B/84C/84D
- DARLINGTON
- High DC current gain

APPLICATIONS

- For use in power linear and switching applications.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

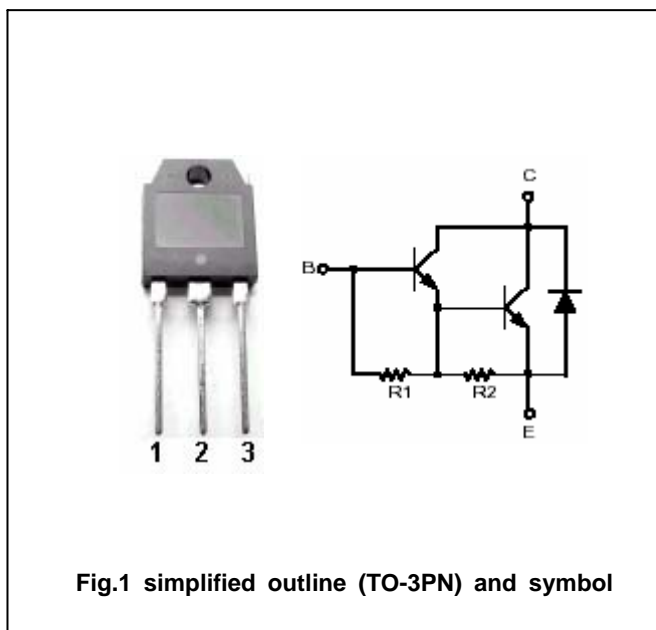


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Tc=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	BDW83	45	V
		BDW83A	60	
		BDW83B	80	
		BDW83C	100	
		BDW83D	120	
V _{CEO}	Collector-emitter voltage	BDW83	45	V
		BDW83A	60	
		BDW83B	80	
		BDW83C	100	
		BDW83D	120	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		15	A
I _B	Base current		0.5	A
P _C	Collector power dissipation	T _C =25	150	W
		T _a =25	3.5	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

Silicon NPN Power Transistors

BDW83/83A/83B/83C/83D

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	BDW83	I _C =30mA, I _B =0			V
		BDW83A				
		BDW83B				
		BDW83C				
		BDW83D				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =6A, I _B =12mA			2.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =15A, I _B =150mA			4.0	V
V _{BE}	Base-emitter on voltage	I _C =6A; V _{CE} =3V			2.5	V
I _{CBO}	Collector cut-off current	BDW83				mA
		BDW83A				
		BDW83B				
		BDW83C				
		BDW83D				
I _{CEO}	Collector cut-off current	BDW83				mA
		BDW83A				
		BDW83B				
		BDW83C				
		BDW83D				
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			2	mA
h _{FE-1}	DC current gain	I _C =6A; V _{CE} =3V	750		20000	
h _{FE-2}	DC current gain	I _C =15A; V _{CE} =3V	100			
V _{EC}	Diode forward voltage	I _E =15A			3.5	V
t _{on}	Turn-on time	I _C = 10 A, I _{B1} = -I _{B2} = 40 mA R _L = 3 Ω; V _{BE(off)} = -4.2V Duty Cycle 2%		0.9		μs
t _{off}	Turn-off time			7.0		μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	0.83	/W

Silicon NPN Power Transistors

BDW83/83A/83B/83C/83D

PACKAGE OUTLINE

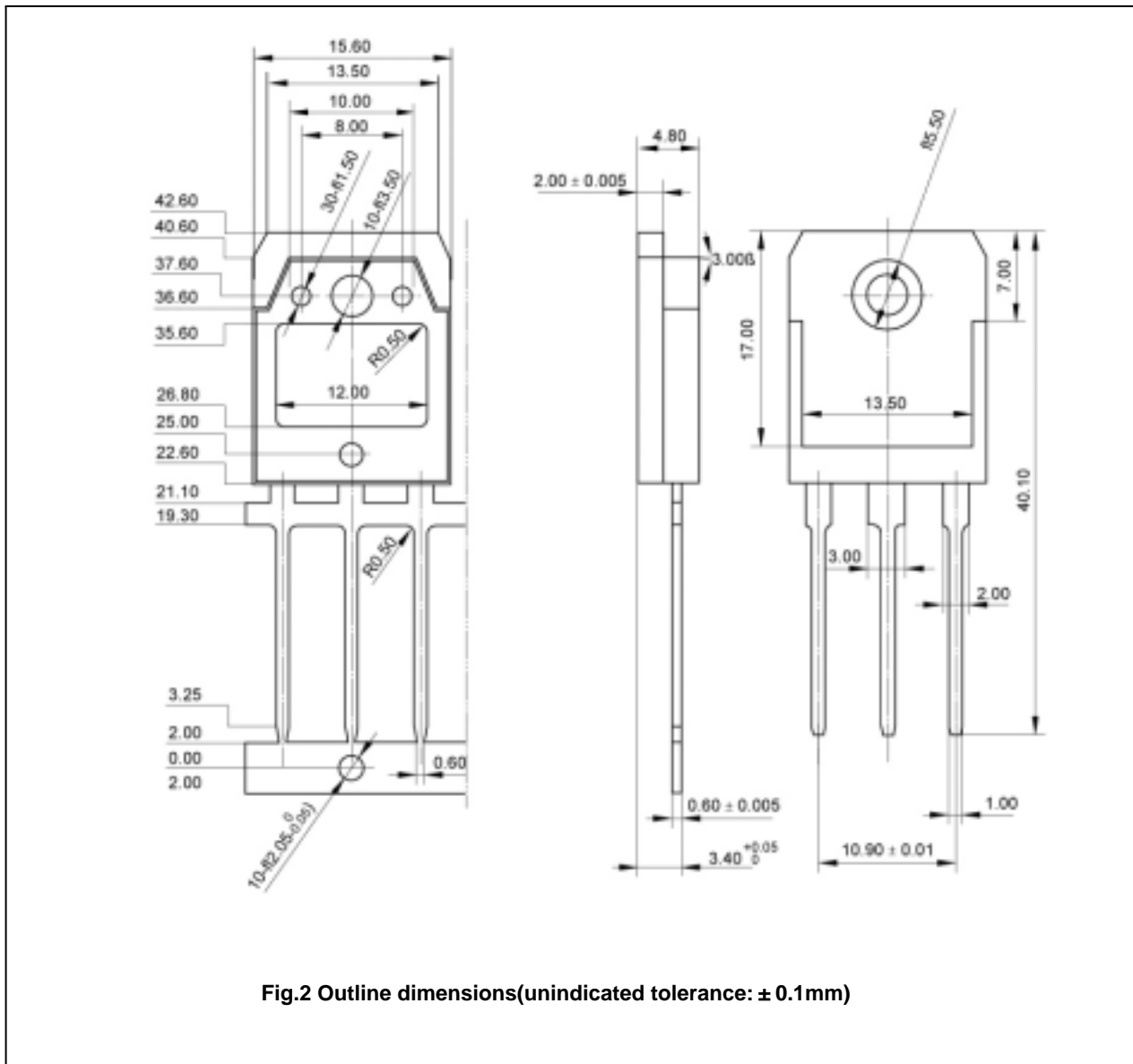


Fig.2 Outline dimensions(unindicated tolerance: ± 0.1mm)